

查询"2SB1205R"供应商

	No.2114B	2SB1205
		PNP Epitaxial Planar Silicon Transistor Strobe High-Current Switching Applications

Applications

- . Strobe, voltage regulators, relay drivers, lamp drivers.

Features

- . Adoption of FBET, MBIT processes.
- . Low saturation voltage.
- . Fast switching speed.
- . Large current capacity.
- . Small and slim package making it easy to make 2SB1205-applied sets smaller.

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CB0}	-25	V
Collector to Emitter Voltage	V_{CE0}	-20	V
Emitter to Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-5	A
Collector Current(Pulse)	I_{CP}	-8	A
Base Current	I_B	-0.5	A
Collector Dissipation	P_C	1	W
		10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

 $T_c=25^\circ\text{C}$ **Electrical Characteristics at $T_a=25^\circ\text{C}$**

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB}=-20\text{V}, I_E=0$			-500	nA
Emitter Cutoff Current	I_{EB0}	$V_{EB}=-4\text{V}, I_C=0$			-500	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=500\text{mA}$	100*		400*	
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-4\text{A}$	60			
Gain-Bandwidth Product	f_T	$V_{CE}=-5\text{V}, I_C=-200\text{mA}$		320		MHz
Output Capacitance	c_{ob}	$V_{CE}=-10\text{V}, f=1\text{MHz}$		60		pF

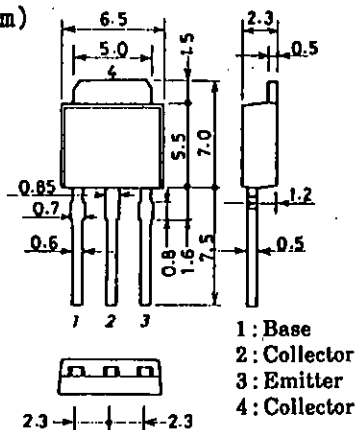
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* The 2SB1205 is classified by 500mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400
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Package Dimensions 2045B

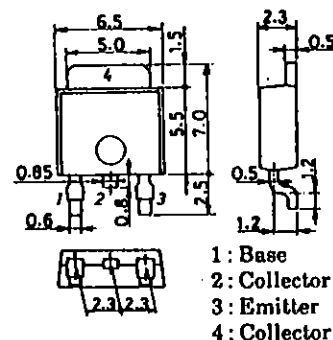
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SANYO: TP

Package Dimensions 2044B

(unit:mm)



SANYO: TP-FA

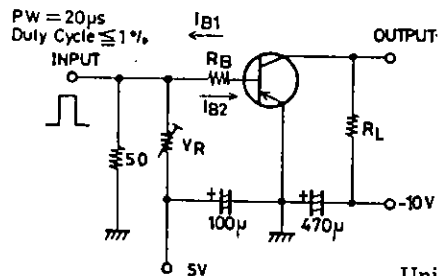
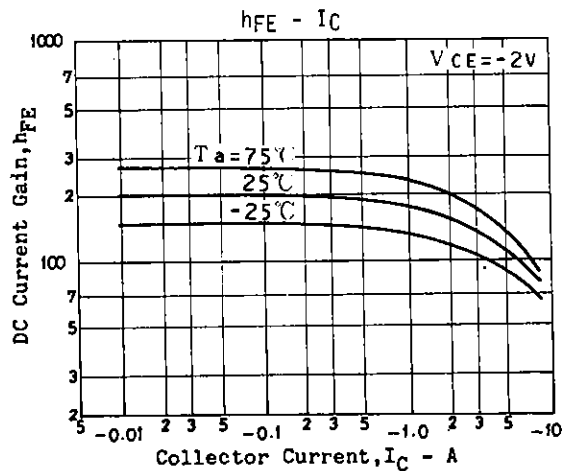
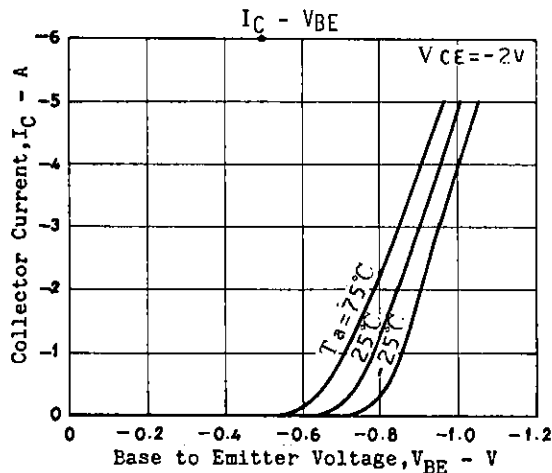
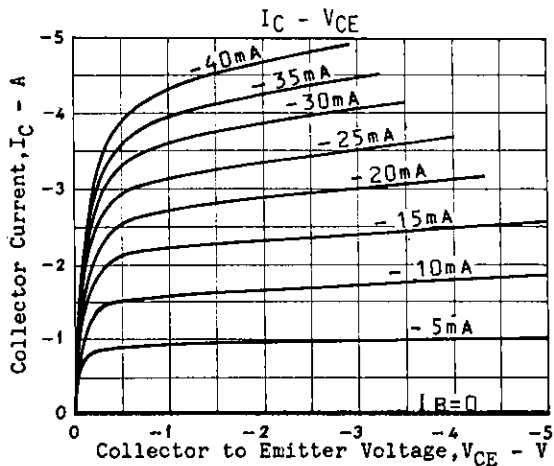
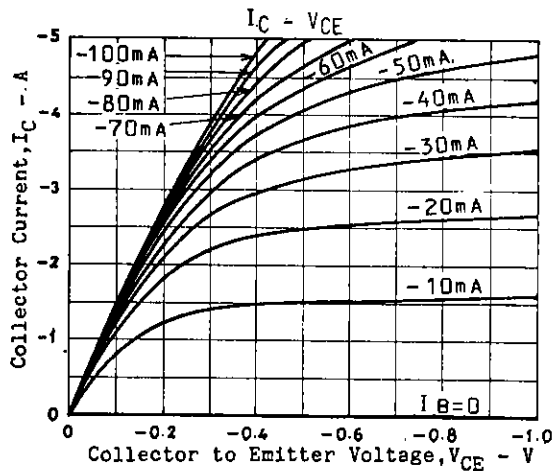
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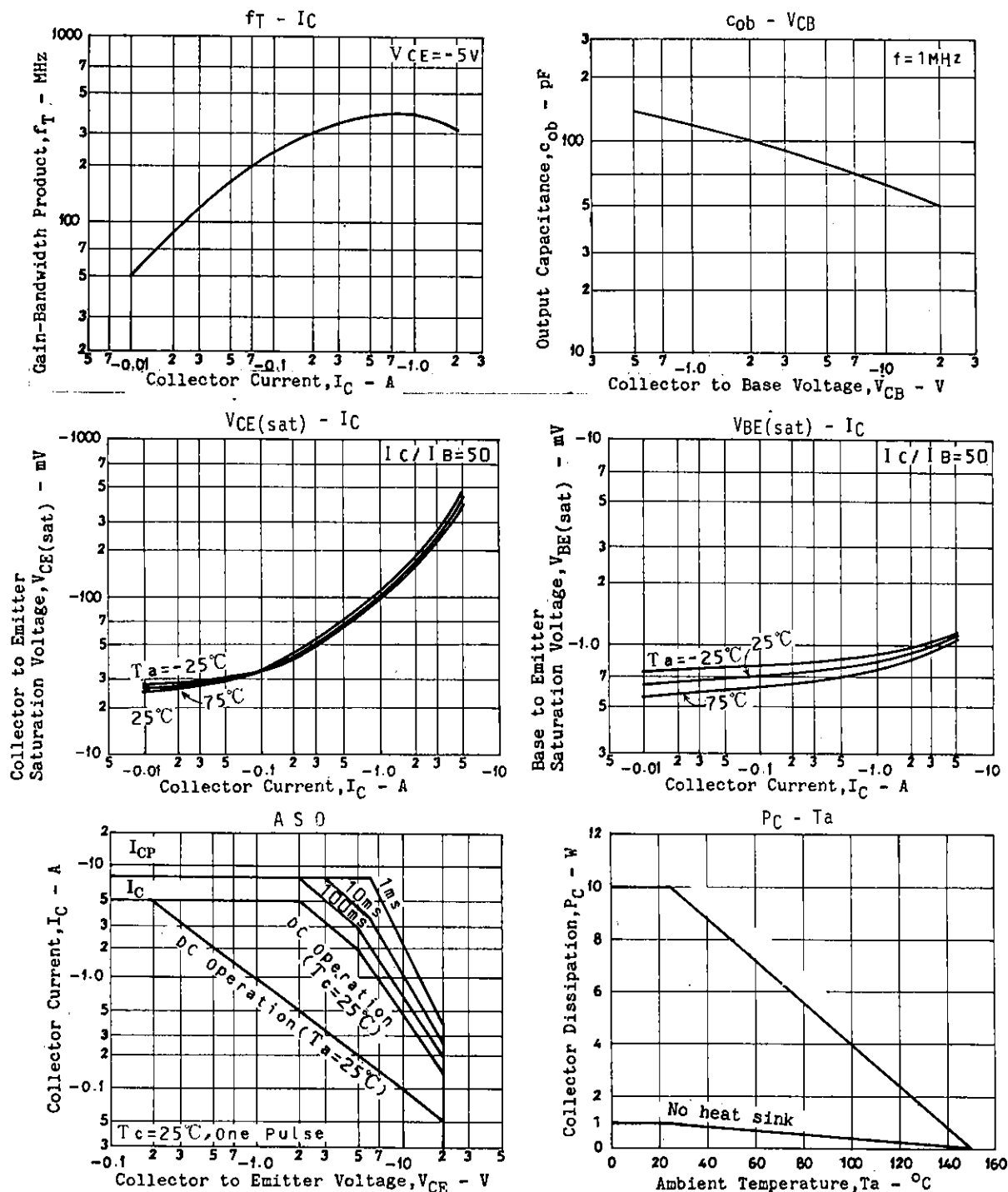
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			min	typ	max	unit
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -60mA$		-250	-500	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = -60mA$		-1.0	-1.3	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, R_{BE} = \infty$	-20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		40		ns
Storage Time	t_{stg}	"		200		ns
Fall Time	t_f	"		10		ns

Switching Time Test Circuit

 $I_C = -10A, I_{B1} = 10A, I_{B2} = -2A$ Unit (Resistance : Ω , Capacitance : F)



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